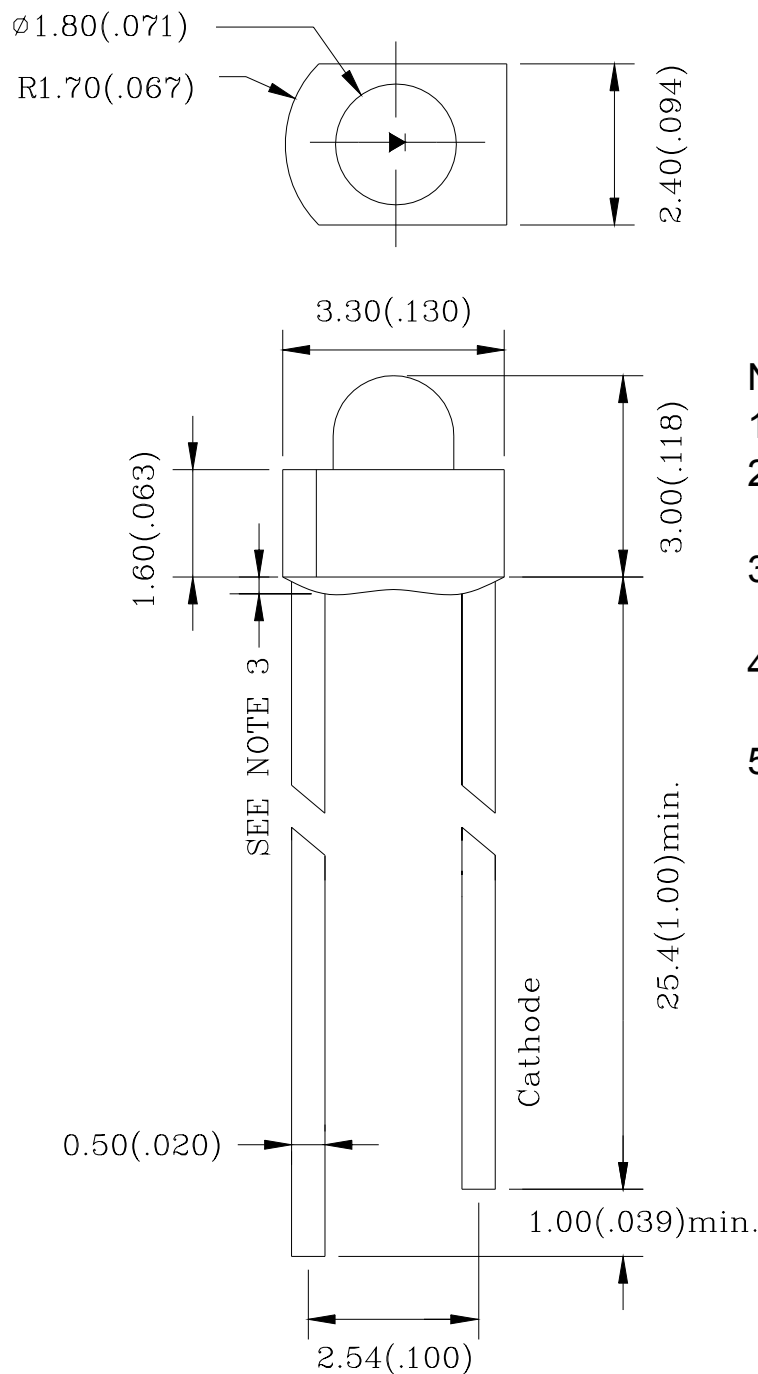


PACKAGE DIMENSIONS**Note:**

- 1.All Dimensions are in millimeters.
- 2.Tolerance is $\pm 0.25\text{mm}(0.010 \text{ "})$ Unless otherwise specified.
- 3.Protruded resin under flange is $1.5\text{mm}(0.059 \text{ "})$ max.
- 4.Lead spacing is measured where the leads emerge from the package.
- 5.Specification are subject to change without notice



Light Emitting Diode Lamp

FEATURES

- * 1.8 mm DIA TOWER TYPE LED LAMP
- * LOW POWER CONSUMPTION
- * I.C. COMPATIBLE
- * LONG LIFE SOLID STATE RELIABILITY

CHIP MATERIALS

- * Dice Material : GaAsP/GaP
- * Light Color : HI.EFFI RED
- * Lens Color : RED DIFFUSED

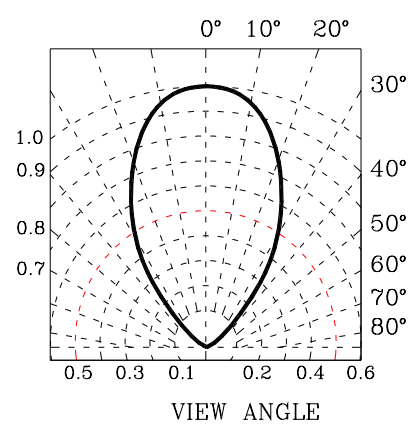
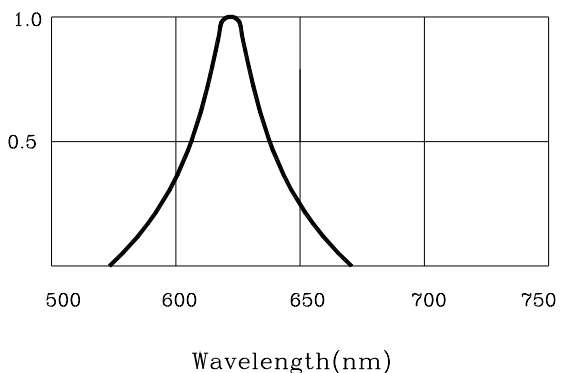
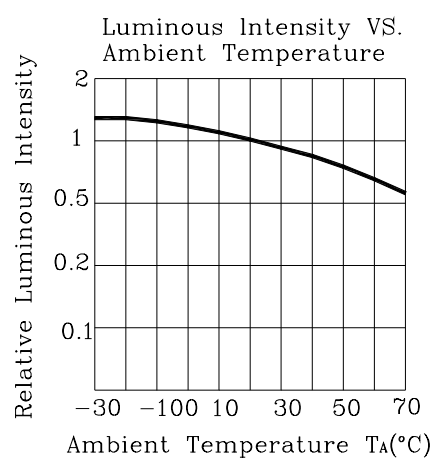
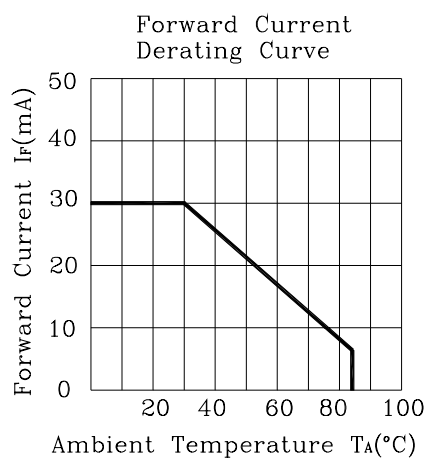
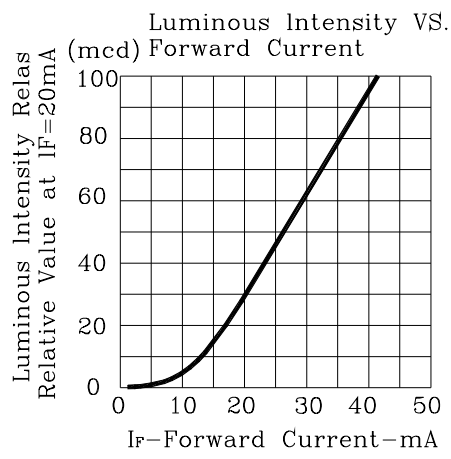
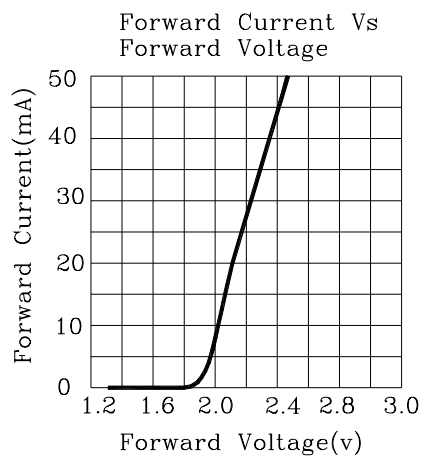
ABSOLUTE MAXIMUM RATING : (Ta = 25 C)

SYMBOL	PARAMETER	HI.EFFI RED	UNIT
PAD	Power Dissipation Per Chip	85	mW
VR	Reverse Voltage Per Chip	5	V
IAF	Continuous Forward Current Per Chip	30	mA
IPF	Peak Forward Current Per Chip (Duty – 0.1,1KHz)	120	mA
–	Derating Linear From 25 C Per Chip	0.40	mA/ C
Topr	Operating Temperature Range	-25 C to 85 C	
Tstg	Storage Temperature Range	-40 C to 85 C	
Lead Soldering Temperature { 1.6mm(0.063 inch) From Body } 260°C ± 5°C for 5 Seconds			

ELECTRO-OPTICAL CHARACTERISTICS : (Ta = 25 C)

SYMBOL	PARAMETER	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
VF	Forward Voltage	IF = 20mA		2.1	2.8	V
IR	Reverse Current	VR = 5V			100	A
D	Dominant Wavelength	IF = 20mA		622		nm
Δ	Spectral Line Half-Width	IF = 20mA		35		nm
2θ1/2	Half Intensity Angle	IF = 20mA		60		deg
IV	Luminous Intensity	IF = 20mA		30		mcd

PART NUMBER : 4-25-CD45R



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